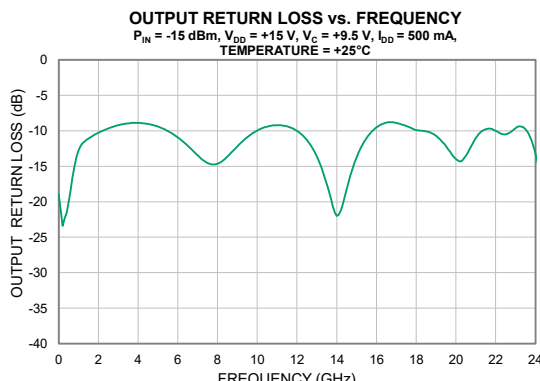
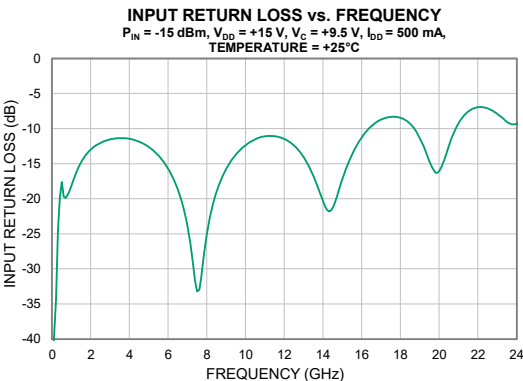
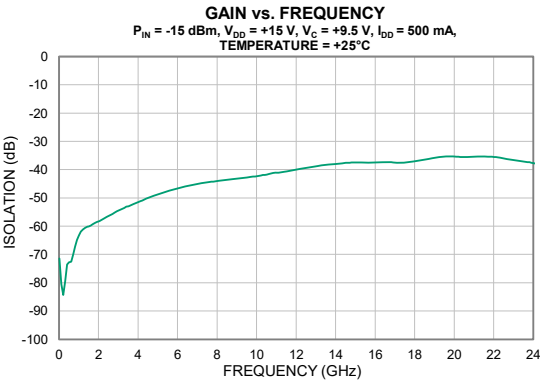
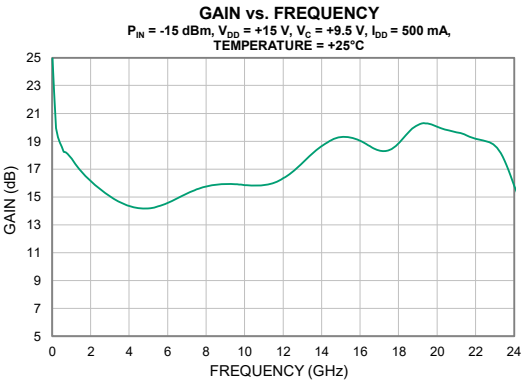


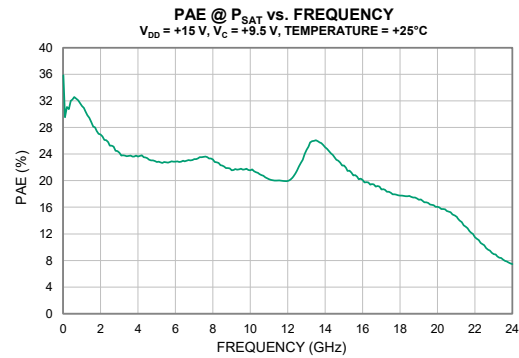
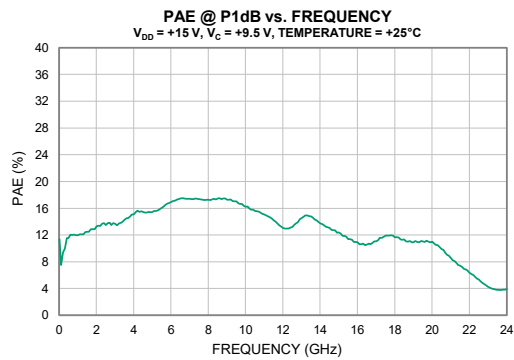
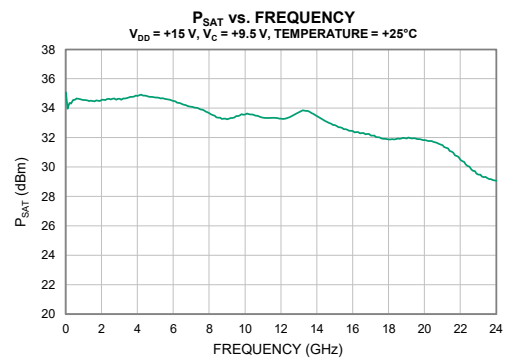
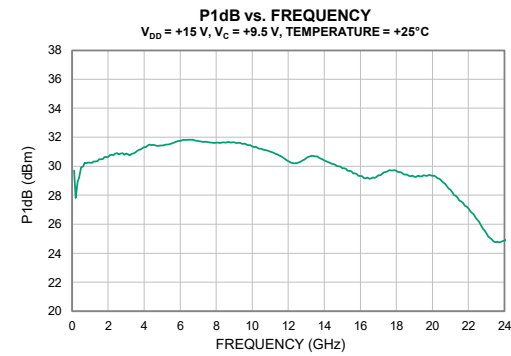
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits DIE Characterization Test Board with external bias tee. All data taken at nominal condition of  $V_{DD} = +15\text{ V}$ ,  $V_C = +9.5\text{ V}$ ,  $V_G$  was adjusted at each voltage and temperature level to achieve  $I_{DD} = 500\text{ mA}$ .



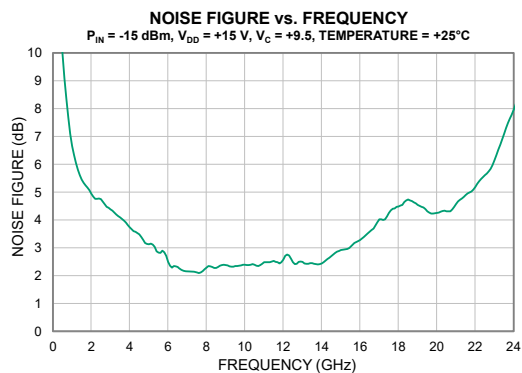
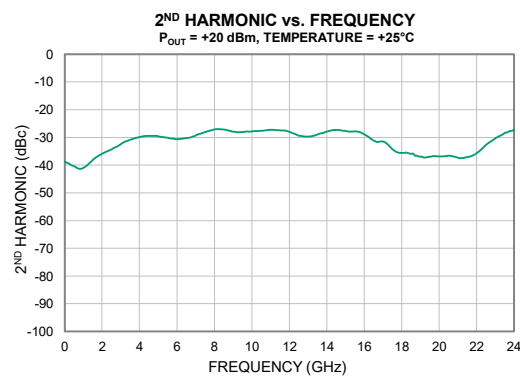
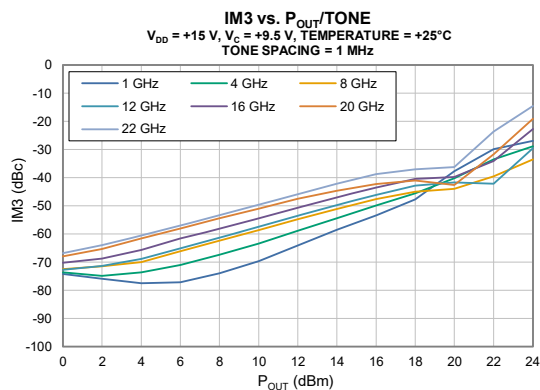
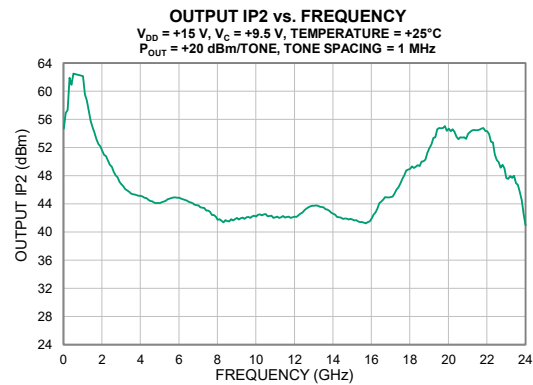
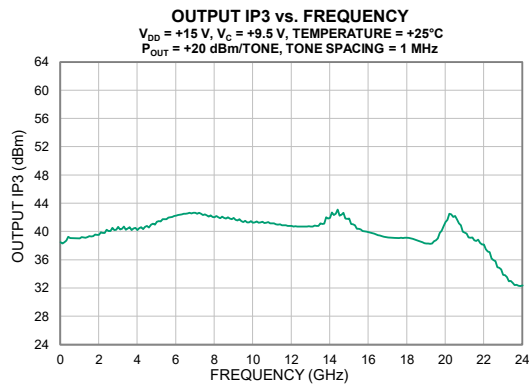
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